

D² 43. (Twice Amended) A method of manufacturing a display device comprising the steps of:

forming a thin film transistor over a substrate;

forming a pixel electrode electrically connected to the thin film transistor;

forming a body with a textured surface on the pixel electrode by a photolithography;

forming a light reflection film on the body with the textured surface; and

flattening a surface of the light reflection film by a CMP process.

D³ 50. (Twice Amended) A method of manufacturing a display device comprising the steps of:

forming a thin film transistor over a substrate;

forming a pixel electrode electrically connected to the thin film transistor;

forming a body with a textured surface on the pixel electrode by a photolithography; and

forming a light reflection film on the body with the textured surface,

wherein the light reflection film has a higher refractive index than the body with the textured

surface.

D⁴ 57. (Twice Amended) A method of manufacturing a display device comprising the steps of:

forming an insulated gate field effect transistor on a semiconductor substrate;

forming a pixel electrode electrically connected to the insulated gate field effect transistor;

forming a body with a textured surface on the pixel electrode by a photolithography; and

forming a light reflection film on the body with the textured surface.

D⁵ 64. (Twice Amended) A method of manufacturing a display device comprising the steps of:

forming an insulated gate field effect transistor on a semiconductor substrate;

forming a pixel electrode electrically connected to the insulated gate field effect transistor;

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forming a body with a textured surface on the pixel electrode by a photolithography;
forming a light reflection film on the body with the textured surface; and
flattening a surface of the light reflection film by a CMP process.

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71.(Twice Amended) A method of manufacturing a display device comprising the steps of:
forming an insulated gate field effect transistor on a semiconductor substrate;
forming a pixel electrode electrically connected to the insulated gate field effect transistor;
forming a body with a textured surface on the pixel electrode by a photolithography; and
forming a light reflection film on the body with the textured surface,
wherein the light reflection film has a higher refractive index than the body with the textured
surface.

Please add the following new claims: /

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78.(New) A method according to claim 36, wherein the light reflection film is formed by one
selected from the group consisting of a sputtering method, a coating method, and a vacuum
evaporation method.

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79.(New) A method according to claim 43, wherein the light reflection film is formed by one
selected from the group consisting of a sputtering method, a coating method, and a vacuum
evaporation method.

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80.(New) A method according to claim 50, wherein the light reflection film is formed by one
selected from the group consisting of a sputtering method, a coating method, and a vacuum
evaporation method.

32 — 81.(New) A method according to claim 57, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

40 — 82.(New) A method according to claim 64, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

48 — 83.(New) A method according to claim 71, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

REMARKS

In the Final Rejection, the Examiner rejects Claims 36-77 under the judicially created doctrine of double patenting over claims 1-81 of U.S. Patent 6,384,886. This rejection is respectfully traversed.

Applicants have now amended each of the independent claims pending in this application to include the limitation of "forming a body with a textured surface on the pixel electrode by a photolithography". This limitation is supported in the specification for example at page 15, lns. 5 - 8. The claims of the '886 patent do not recite such a limitation. Therefore, it is respectfully requested that this rejection be withdrawn, and the application allowed.

New Claims

The fee for new claims has been calculated as shown below. These dependent claims are directed to the limitation removed from the independent claims.